Kazhuhiko Endo

List of Publications by Year
in descending order

195	3,128	201385	214527
papers	citations	27 h-index	47 g-index

195	195	195	2257
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics. Journal of Applied Physics, 1995, 78, 1370-1372.	1.1	165
2	Grain-Orientation Induced Work Function Variation in Nanoscale Metal-Gate Transistorsâ€"Part I: Modeling, Analysis, and Experimental Validation. IEEE Transactions on Electron Devices, 2010, 57, 2504-2514.	1.6	156
3	Plasma deposition of low-dielectric-constant fluorinated amorphous carbon. Journal of Applied Physics, 1999, 86, 2739-2745.	1.1	132
4	Demonstration, Analysis, and Device Design Considerations for Independent DG MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 2046-2053.	1.6	115
5	A novel method for the 3-dimensional simulation of orthognathic surgery by using a multimodal image-fusion technique. American Journal of Orthodontics and Dentofacial Orthopedics, 2006, 130, 786-798.	0.8	100
6	Fluorinated amorphous carbon thin films grown by helicon plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics. Applied Physics Letters, 1996, 68, 2864-2866.	1.5	94
7	Investigation of the TiN Gate Electrode With Tunable Work Function and Its Application for FinFET Fabrication. IEEE Nanotechnology Magazine, 2006, 5, 723-730.	1.1	90
8	Modeling and analysis of grain-orientation effects in emerging metal-gate devices and implications for SRAM reliability. , 2008, , .		87
9	Inhibition of enamel demineralization by buffering effect of Sâ€‹scp›PRG‹/scp› fillerâ€‹containing dental sealant. European Journal of Oral Sciences, 2014, 122, 78-83.	0.7	83
10	Grain-Orientation Induced Work Function Variation in Nanoscale Metal-Gate Transistorsâ€"Part II: Implications for Process, Device, and Circuit Design. IEEE Transactions on Electron Devices, 2010, 57, 2515-2525.	1.6	78
11	Fluorinated Amorphous Carbon as a Low-Dielectric-Constant Interlayer Dielectric. MRS Bulletin, 1997, 22, 55-58.	1.7	66
12	Variability Analysis of TiN Metal-Gate FinFETs. IEEE Electron Device Letters, 2010, 31, 546-548.	2.2	63
13	Analytical Thermal Model for Self-Heating in Advanced FinFET Devices With Implications for Design and Reliability. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2013, 32, 1045-1058.	1.9	57
14	Tenâ€‹years degradation of resinâ€"dentin bonds. European Journal of Oral Sciences, 2010, 118, 404-410.	0.7	56
15	Performance Enhancement of Tunnel Field-Effect Transistors by Synthetic Electric Field Effect. IEEE Electron Device Letters, 2014, 35, 792-794.	2.2	53
16	Cointegration of High-Performance Tied-Gate Three-Terminal FinFETs and Variable Threshold-Voltage Independent-Gate Four-Terminal FinFETs With Asymmetric Gate-Oxide Thicknesses. IEEE Electron Device Letters, 2007, 28, 517-519.	2.2	48
17	A review: Biodegradation of resinâ€"dentin bonds. Japanese Dental Science Review, 2011, 47, 5-12.	2.0	40
18	Amorphous carbon thin films containing benzene rings for use as low-dielectric-constant interlayer dielectrics. Applied Physics Letters, 1997, 70, 2616-2618.	1.5	39

#	Article	IF	Citations
19	Fabrication of FinFETs by Damage-Free Neutral-Beam Etching Technology. IEEE Transactions on Electron Devices, 2006, 53, 1826-1833.	1.6	37
20	Application of Fluorinated Amorphous Carbon Thin Films for Low Dielectric Constant Interlayer Dielectrics. Japanese Journal of Applied Physics, 1998, 37, 1809-1814.	0.8	35
21	In vitro degradation of resinâ€“dentin bonds with oneâ€bottle selfâ€etching adhesives. European Journal of Oral Sciences, 2009, 117, 611-617.	0.7	35
22	Nitrogen doped fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics. Applied Physics Letters, 1996, 68, 3656-3658.	1.5	33
23	Modeling and Analysis of Self-Heating in FinFET Devices for Improved Circuit and EOS/ESD Performance. , 2007, , .		33
24	Impacts of plasma-induced damage due to UV light irradiation during etching on Ge fin fabrication and device performance of Ge fin field-effect transistors. Applied Physics Express, 2017, 10, 026501.	1.1	33
25	On the gate-stack origin threshold voltage variability in scaled FinFETs and multi-FinFETs. , 2010, , .		32
26	Corrosion Behavior and Surface Structure of Orthodontic Ni-Ti Alloy Wires.. Dental Materials Journal, 2001, 20, 103-113.	0.8	30
27	Enhancing SRAM cell performance by using independent double-gate FinFET. , 2008, , .		30
28	Effect of Cr and Cu Addition on Corrosion Behavior of Ni-Ti Alloys.. Dental Materials Journal, 1998, 17, 31-40.	0.8	29
29	Design Optimization of FinFET Domino Logic Considering the Width Quantization Property. IEEE Transactions on Electron Devices, 2010, 57, 2934-2943.	1.6	29
30	Metal Organic Atomic Layer Deposition of High-k Gate Dielectrics Using Plasma Oxidation. Japanese Journal of Applied Physics, 2003, 42, L685-L687.	0.8	28
31	Advanced FinFET CMOS Technology: TiN-Gate, Fin-Height Control and Asymmetric Gate Insulator Thickness 4T-FinFETs. , 2006, , .		28
32	Experimental Evaluation of Effects of Channel Doping on Characteristics of FinFETs. IEEE Electron Device Letters, 2007, 28, 1123-1125.	2.2	28
33	Corrosion behavior of ion implanted nickel-titanium orthodontic wire in fluoride mouth rinse solutions. Dental Materials Journal, 2010, 29, 53-58.	0.8	28
34	In Vitro Corrosion Characteristics of Commercially Available Orthodontic Wires. Dental Materials Journal, 2004, 23, 197-202.	0.8	27
35	Nanoscale Wet Etching of Physical-Vapor-Deposited Titanium Nitride and Its Application to Sub-30-nm-Gate-Length Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Fabrication. Japanese Journal of Applied Physics, 2010, 49, 06GH18.	0.8	27
36	Decomposition of On-Current Variability of nMOS FinFETs for Prediction Beyond 20 nm. IEEE Transactions on Electron Devices, 2012, 59, 2003-2010.	1.6	27

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37	Inhibition of enamel demineralization and bond-strength properties of bioactive glass containing 4-META/MMA-TBB-based resin adhesive. European Journal of Oral Sciences, 2015, 123, 202-207.	0.7	27
38	Galvanic corrosion behavior of orthodontic archwire alloys coupled to bracket alloys. Angle Orthodontist, 2006, 76, 705-11.	1.1	27
39	Independent-Double-Gate FinFET SRAM for Leakage Current Reduction. IEEE Electron Device Letters, 2009, 30, 757-759.	2.2	24
40	A Comparative Study of Nitrogen Gas Flow Ratio Dependence on the Electrical Characteristics of Sputtered Titanium Nitride Gate Bulk Planar Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors and Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2009, 48, 05DC01.	0.8	23
41	Fluctuation Analysis of Parasitic Resistance in FinFETs With Scaled Fin Thickness. IEEE Electron Device Letters, 2009, 30, 407-409.	2.2	23
42	Frictional and mechanical properties of diamond-like carbon-coated orthodontic brackets. European Journal of Orthodontics, 2013, 35, 216-222.	1.1	23
43	Preparation And Properties Of Fluorinated Amorphous Carbon Thin Films By Plasma Enhanced Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 381, 249.	0.1	22
44	Dopant profiling in vertical ultrathin channels of double-gate metalâ€“oxideâ€“semiconductor field-effect transistors by using scanning nonlinear dielectric microscopy. Applied Physics Letters, 2004, 85, 4139-4141.	1.5	22
45	Investigation of Low-Energy Tilted Ion Implantation for Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Extension Doping. Japanese Journal of Applied Physics, 2010, 49, 04DC18.	0.8	22
46	Suppressing V<inf>t</inf> and G<inf>m</inf> variability of FinFETs using amorphous metal gates for 14 nm and beyond. , 2012, , .		22
47	Application of Plasma Immersion Ion Implantation for Surface Modification of Nickel-titanium Rotary Instruments. Dental Materials Journal, 2007, 26, 467-473.	0.8	21
48	Low Temperature, Beam-Orientation-Dependent, Lattice-Plane-Independent, and Damage-Free Oxidation for Three-Dimensional Structure by Neutral Beam Oxidation. Japanese Journal of Applied Physics, 2009, 48, 04C007.	0.8	21
49	Low activation energy, high-quality oxidation of Si and Ge using neutral beam. Applied Physics Letters, 2011, 98, 203111.	1.5	21
50	Nitrogen Gas Flow Ratio and Rapid Thermal Annealing Temperature Dependences of Sputtered Titanium Nitride Gate Work Function and Their Effect on Device Characteristics. Japanese Journal of Applied Physics, 2008, 47, 2433.	0.8	20
51	Controlling Fluorine Concentration of Fluorinated Amorphous Carbon Thin Films for Low Dielectric Constant Interlayer Dielectrics. Japanese Journal of Applied Physics, 1997, 36, L1531-L1533.	0.8	19
52	Experimental Study of Effective Carrier Mobility of Multi-Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors with (111) Channel Surface Fabricated by Orientation-Dependent Wet Etching. Japanese Journal of Applied Physics, 2006, 45, 3084-3087.	0.8	18
53	Four-Terminal FinFETs Fabricated Using an Etch-Back Gate Separation. IEEE Nanotechnology Magazine, 2007, 6, 201-205.	1.1	18
54	Responses of RAW264.7 macrophages to waterâ€dispersible gold and silver nanoparticles stabilized by metalâ€“carbon Ïƒâ€bonds. Journal of Biomedical Materials Research - Part A, 2014, 102, 1838-1849.	2.1	18

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55	Effect of dentinal water on bonding of self-etching adhesives. Dental Materials Journal, 2009, 28, 634-641.	0.8	17
56	Grain-Orientation Induced Quantum Confinement Variation in FinFETs and Multi-Gate Ultra-Thin Body CMOS Devices and Implications for Digital Design. IEEE Transactions on Electron Devices, 2011, 58, 2282-2292.	1.6	17
57	Variability Origins of Parasitic Resistance in FinFETs With Silicided Source/Drain. IEEE Electron Device Letters, 2012, 33, 474-476.	2.2	15
58	Suppression of threshold voltage variability of double-gate fin field-effect transistors using amorphous metal gate with uniform work function. Applied Physics Letters, 2013, 102, .	1.5	15
59	Introduction of SiGe/Si heterojunction into novel multilayer tunnel FinFET. Japanese Journal of Applied Physics, 2016, 55, 04EB06.	0.8	15
60	Tunnel FinFET CMOS inverter with very low short-circuit current for ultralow-power Internet of Things application. Japanese Journal of Applied Physics, 2017, 56, 04CD19.	0.8	15
61	Atomic layer germanium etching for 3D Fin-FET using chlorine neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	0.9	15
62	Corrosion Characteristics of Ferric and Austenitic Stainless Steels for Dental Magnetic Attachment.. Dental Materials Journal, 2000, 19, 34-49.	0.8	14
63	Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653.	1.6	14
64	Robust FinFET SRAM design based on dynamic back-gate voltage adjustment. Microelectronics Reliability, 2014, 54, 2604-2612.	0.9	14
65	Silicon nanodisk array with a fin field-effect transistor for time-domain weighted sum calculation toward massively parallel spiking neural networks. Applied Physics Express, 2016, 9, 034201.	1.1	14
66	Plasma fluorination of polyimide thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 3134-3137.	0.9	13
67	Deposition of silicon dioxide films on amorphous carbon films by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics. Applied Physics Letters, 1997, 70, 1078-1079.	1.5	13
68	Enhancement of FinFET performance using 25-nm-thin sidewall spacer grown by atomic layer deposition. Solid-State Electronics, 2012, 74, 13-18.	0.8	13
69	Electrochemical and surface studies on the passivity of a dental Pd-based casting alloy in alkaline sulphide solution. Corrosion Science, 2003, 45, 1491-1504.	3.0	12
70	Work function controllability of metal gates made by interdiffusing metal stacks with low and high work functions. Microelectronic Engineering, 2005, 80, 284-287.	1.1	12
71	Threshold-Voltage Reduction of FinFETs by Ta/Mo Interdiffusion Dual Metal-Gate Technology for Low-Operating-Power Application. IEEE Transactions on Electron Devices, 2008, 55, 2454-2461.	1.6	12
72	Variation analysis of TiN FinFETs. , 2009, , .		12

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73	Experimental Study of Physical-Vapor-Deposited Titanium Nitride Gate with An n⁺-Polycrystalline Silicon Capping Layer and Its Application to 20 nm Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC14.	0.8	12
74	Variability Analysis of Scaled Crystal Channel and Poly-Si Channel FinFETs. IEEE Transactions on Electron Devices, 2012, 59, 573-581.	1.6	12
75	Influence of work function variation of metal gates on fluctuation of sub-threshold drain current for fin field-effect transistors with undoped channels. Japanese Journal of Applied Physics, 2014, 53, 04EC11.	0.8	12
76	Adhesion of Adhesive Resin to Dental Precious Metal Alloys. Part I. New Precious Metal Alloys with Base Metals for Resin Bonding.. Dental Materials Journal, 1998, 17, 275-284.	0.8	11
77	Deoxidization of Cu Oxide under Extremely Low Oxygen Pressure Ambient. Japanese Journal of Applied Physics, 2006, 45, L393-L395.	0.8	10
78	Crystal growth by restorative filling materials. European Journal of Oral Sciences, 2010, 118, 489-493.	0.7	10
79	Demonstration of Split-Gate Type Trigate Flash Memory With Highly Suppressed Over-Erase. IEEE Electron Device Letters, 2012, 33, 345-347.	2.2	10
80	Fabrication of a Vertical-Channel Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor Using a Neutral Beam Etching. Japanese Journal of Applied Physics, 2006, 45, L279-L281.	0.8	9
81	A Dynamical Power-Management Demonstration Using Four-Terminal Separated-Gate FinFETs. IEEE Electron Device Letters, 2007, 28, 452-454.	2.2	9
82	A Ta/Mo Interdiffusion Dual Metal Gate Technology for Drivability Enhancement of FinFETs. IEEE Electron Device Letters, 2008, 29, 618-620.	2.2	9
83	Multidomain Dynamics of Ferroelectric Polarization and its Coherency-Breaking in Negative Capacitance Field-Effect Transistors. , 2018, , .		9
84	Changes in transition temperature of the Si(111)1 Ã— 1âˆ’7 Ã— 7 phase transition observed under various oxygen environments. Surface Science, 1995, 328, L553-L560.	0.8	8
85	Investigation of N-Channel Triple-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors on (100) Silicon On Insulator Substrate. Japanese Journal of Applied Physics, 2006, 45, 3097-3100.	0.8	8
86	Atomic Layer Deposition of SiO₂ for the Performance Enhancement of Fin Field Effect Transistors. Japanese Journal of Applied Physics, 2013, 52, 116503.	0.8	8
87	Steep switching less than 15 mV dec^{âˆ’1} in silicon-on-insulator tunnel FETs by a trimmed-gate structure. Japanese Journal of Applied Physics, 2019, 58, SBBA16.	0.8	8
88	High Electron Mobility Germanium FinFET Fabricated by Atomic Layer Defect-Free and Roughness-Free Etching. IEEE Open Journal of Nanotechnology, 2021, 2, 26-30.	0.9	8
89	Low-k fluorinated amorphous carbon interlayer technology for quarter micron devices. , 0, , .		7
90	Damage-free neutral beam etching technology for high mobility FinFETs. , 0, , .		7

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91	Fabrication and characterization of vertical-type double-gate metal-oxide-semiconductor field-effect transistor with ultrathin Si channel and self-aligned source and drain. Applied Physics Letters, 2006, 88, 072103.	1.5	7
92	Design of SOI FinFET on 32nm technology node for low standby power (LSTP) operation considering gate-induced drain leakage (GIDL). Solid-State Electronics, 2010, 54, 1060-1065.	0.8	7
93	Investigation of Thermal Stability of TiN Film Formed by Atomic Layer Deposition Using Tetrakis(dimethylamino)titanium Precursor for Metal-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 04DA16.	0.8	7
94	Advanced FinFET process technology for 20 nm node and beyond. , 2011, , .		7
95	Comprehensive analysis of I<inf>on</inf> variation in metal gate FinFETs for 20nm and beyond. , 2011, , .		7
96	Performance evaluation of parallel electric field tunnel field-effect transistor by a distributed-element circuit model. Solid-State Electronics, 2014, 102, 82-86.	0.8	7
97	Impact of granular work function variation in a gate electrode on low-frequency noise for fin field-effect transistors. Applied Physics Express, 2015, 8, 044201.	1.1	7
98	Room-temperature and high-quality HfO2/SiO2 gate stacked film grown by neutral beam enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	7
99	Effect of Bias Addition on the Gap-Filling Properties of Fluorinated Amorphous Carbon Thin Films Grown by Helicon Wave Plasma-Enhanced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1996, 35, L1348-L1350.	0.8	6
100	Impact of extension and source/drain resistance on FinFET performance. , 2008, , .		6
101	Fabrication and Characterization of NOR-Type Tri-Gate Flash Memory with Improved Inter-Poly Dielectric Layer by Rapid Thermal Oxidation. Japanese Journal of Applied Physics, 2012, 51, 06FE19.	0.8	6
102	Improvement of epitaxial channel quality on heavily arsenic- and boron-doped Si surfaces and impact on performance of tunnel field-effect transistors. Solid-State Electronics, 2015, 113, 173-178.	0.8	6
103	Spike-based time-domain weighted-sum calculation using nanodevices for low power operation. , 2016, , .		6
104	Experimental Study of Physical-Vapor-Deposited Titanium Nitride Gate with An n+-Polycrystalline Silicon Capping Layer and Its Application to 20 nm Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC14.	0.8	6
105	Treatment of the wall materials of extremely high vacuum chamber for dynamical surface analysis. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 417-421.	0.9	5
106	Fluorinated Amorphous Carbon Thin Films Grown from C4F8 for Multilevel Interconnections of Integrated Circuits. Materials Research Society Symposia Proceedings, 1996, 443, 165.	0.1	5
107	Demonstration and Analysis of Accumulation-Mode Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2006, 45, 3079-3083.	0.8	5
108	New Fabrication Technology of Fin Field Effect Transistors Using Neutral-Beam Etching. Japanese Journal of Applied Physics, 2006, 45, 5513-5516.	0.8	5

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109	Comparative Study of Charge Trapping Type SOI-FinFET Flash Memories with Different Blocking Layer Materials. Journal of Low Power Electronics and Applications, 2014, 4, 153-167.	1.3	5
110	Steep switching in trimmed-gate tunnel FET. AIP Advances, 2018, 8, .	0.6	5
111	Ta/Mo Stack Dual Metal Gate Technology Applicable to Gate-First Processes. Japanese Journal of Applied Physics, 2007, 46, 1825-1829.	0.8	4
112	Dual-Metal-Gate Transistors with Symmetrical Threshold Voltages Using Work-Function-Tuned Ta/Mo Bilayer Metal Gates. Japanese Journal of Applied Physics, 2008, 47, 2428-2432.	0.8	4
113	Enhancing Noise Margins of Fin-Type Field Effect Transistor Static Random Access Memory Cell by Using Threshold Voltage-Controllable Flexible-Pass-Gates. Applied Physics Express, 2009, 2, 054502.	1.1	4
114	Variability Analysis of TiN FinFET SRAM Cells and Its Compensation by Independent-DG FinFETs. IEEE Electron Device Letters, 2010, 31, 1095-1097.	2.2	4
115	Influence of NiSi on parasitic resistance fluctuation of FinFETs. , 2011, , .		4
116	Independent double-gate FinFET SRAM technology. , 2011, , .		4
117	Scaling breakthrough for analog/digital circuits by suppressing variability and low-frequency noise for FinFETs by amorphous metal gate technology. , 2014, , .		4
118	Heated ion implantation for high-performance and highly reliable silicon-on-insulator complementary metalâ€“oxideâ€“silicon fin field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 04DA06.	0.8	4
119	Atomic layer defect-free etching for germanium using HBr neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 051001.	0.9	4
120	Extremely high vacuum system for dynamical surface analysis. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2655-2658.	0.9	3
121	Time-Dependent Reliability Of The Interface Between A-C:F And Inorganic Dielectrics. Materials Research Society Symposia Proceedings, 1998, 511, 365.	0.1	3
122	Enhancing noise margins of FinFET SRAM by integrating V<inf>th</inf>-controllable flexible-pass-gates. , 2008, , .		3
123	Dual metal gate FinFET integration by Ta/Mo diffusion technology for Vt reduction and multi-Vt CMOS application. Solid-State Electronics, 2009, 53, 701-705.	0.8	3
124	High-frequency characterization of intrinsic FinFET channel. , 2010, , .		3
125	Fin-height controlled PVD-TiN gate finFET SRAM for enhancing noise margin. , 2010, , .		3
126	Variability origins of FinFETs and perspective beyond 20nm node. , 2011, , .		3

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127	A Correlative Analysis Between Characteristics of FinFETs and SRAM Performance. IEEE Transactions on Electron Devices, 2012, 59, 1345-1352.	1.6	3
128	Gate Structure Dependence of Variability in Polycrystalline Silicon Fin-Channel Flash Memories. Japanese Journal of Applied Physics, 2013, 52, 06GE01.	0.8	3
129	Impact of fin length on threshold voltage modulation by back bias for Independent double-gate tunnel fin field-effect transistors. Solid-State Electronics, 2015, 111, 62-66.	0.8	3
130	Preparation by MOCVD and characterization by AFM of the (119) oriented Bi-2223 thin films. Physica C: Superconductivity and Its Applications, 2002, 378-381, 1274-1277.	0.6	2
131	Metal Organic Atomic Layer Deposition of Metal Silicate Film for High-kGate Dielectrics. Japanese Journal of Applied Physics, 2004, 43, L1296-L1298.	0.8	2
132	Demonstration of Dopant Profiling in Ultrathin Channels of Vertical-Type Double-Gate Metal-Oxide-Semiconductor Field-Effect-Transistor by Scanning Nonlinear Dielectric Microscopy. Japanese Journal of Applied Physics, 2005, 44, 2400-2404.	0.8	2
133	Experimental evaluation of parallel transmission using optical ZCZ-CDMA system. , 2009, , .		2
134	Nanoscale TiN wet etching and its application for FinFET fabrication. , 2009, , .		2
135	Vertical ultrathinâ€channel multiâ€gate MOSFETs (MuGFETs): technological challenges and future developments. IEEJ Transactions on Electrical and Electronic Engineering, 2009, 4, 386-391.	0.8	2
136	Atomic layer deposition of 25-nm-thin sidewall spacer for enhancement of FinFET performance. , 2011, , .		2
137	Fabrication of Floating-Gate-Type Fin-Channel Double- and Tri-Gate Flash Memories and Comparative Study of Their Electrical Characteristics. Japanese Journal of Applied Physics, 2012, 51, 04DD03.	0.8	2
138	Experimental Study of Floating-Gate-Type Metalâ€“Oxideâ€“Semiconductor Capacitors with Nanosize Triangular Cross-Sectional Tunnel Areas for Low Operating Voltage Flash Memory Application. Japanese Journal of Applied Physics, 2012, 51, 06FF01.	0.8	2
139	Cryogenic operation of double-gate FinFET and demonstration of analog circuit at 4.2K. , 2012, , .		2
140	Experimental study of three-dimensional fin-channel charge trapping flash memories with titanium nitride and polycrystalline silicon gates. Japanese Journal of Applied Physics, 2014, 53, 04ED16.	0.8	2
141	On the drain bias dependence of long-channel silicon-on-insulator-based tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CD04.	0.8	2
142	Bias temperature instability in tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CA04.	0.8	2
143	Si Nanopillar/SiGe Composite Structure for Thermally Managed Nano-devices. , 2021, , .		2
144	Fabrication and Characterization of NOR-Type Tri-Gate Flash Memory with Improved Inter-Poly Dielectric Layer by Rapid Thermal Oxidation. Japanese Journal of Applied Physics, 2012, 51, 06FE19.	0.8	2

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145	Channel shape and interpoly dielectric material effects on electrical characteristics of floating-gate-type three-dimensional fin channel flash memories. Japanese Journal of Applied Physics, 2015, 54, 04DD04.	0.8	2
146	Experimental Comparisons between Tetrakis(dimethylamino)titanium Precursor-Based Atomic-Layer-Deposited and Physical-Vapor-Deposited Titaniumâ€“Nitride Gate for High-Performance Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA05.	0.8	2
147	Management of Phonon Transport in Lateral Direction for Gap-Controlled Si Nanopillar/SiGe Interlayer Composite Materials. IEEE Open Journal of Nanotechnology, 2021, 2, 148-152.	0.9	2
148	Phenyl Silica Glass for Formation of Porous Dielectric Film. Materials Research Society Symposia Proceedings, 1999, 565, 49.	0.1	1
149	Fluorinated Amorphous Carbon Thin Films for Multilevel Interconnections of Integrated Circuits.. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 1999, 12, 193-198.	0.1	1
150	Atomic Layer Deposition of High-k Gate Dielectrics Using MO Precursor and Cyclic Plasma Exposure. Materials Research Society Symposia Proceedings, 2002, 745, 281.	0.1	1
151	Growth by MOMBE of c-axis superconducting YBCO thin films on different substrates: in situ RHEED monitoring of the growth. IEEE Transactions on Applied Superconductivity, 2003, 13, 2792-2794.	1.1	1
152	A Dynamical Power-Management Demonstration Using Four-Terminal Separated-Gate FinFETs. SOI Conference, Proceedings of the IEEE International, 2006, , .	0.0	1
153	Independent-gate four-terminal FinFET SRAM for drastic leakage current reduction. , 2008, , .		1
154	Realization of 0.7-V analog circuits by adaptive-Vt operation of FinFET. , 2010, , .		1
155	0.5V FinFET SRAM with dynamic threshold control of pass gates for salvaging malfunctioned bits. , 2010, , .		1
156	May the fourth (terminal) be with you - circuit design beyond FinFET. , 2010, , .		1
157	Comparative study of tri-gate flash memories with split and stack gates. , 2011, , .		1
158	Variability analysis of scaled poly-Si channel FinFETs and tri-gate flash memories for high density and low cost stacked 3D-memory application. , 2011, , .		1
159	Correlative analysis between characteristics of 30-nm L<inf>G</inf> FinFETs and SRAM performance. , 2011, , .		1
160	Experimental study of tri-gate SOI-FinFET flash memory. , 2012, , .		1
161	Flexible V<inf>th</inf> FinFETs with 9-nm-thick extremely-thin BOX. , 2012, , .		1
162	Analysis of Threshold Voltage Flexibility in Ultrathin-BOX SOI FinFETs. Journal of Low Power Electronics and Applications, 2014, 4, 110-118.	1.3	1

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163	Defect-free germanium etching for 3D Fin MOSFET using neutral beam etching. , 2016, , .		1
164	Enhancement of capacitance benefit by drain offset structure in tunnel field-effect transistor circuit speed associated with tunneling probability increase. Japanese Journal of Applied Physics, 2018, 57, 04FD13.	0.8	1
165	Microwave Annealing Technologies for Variability Reduction of Nanodevices: A Review of Their Impact on FinFETs. IEEE Nanotechnology Magazine, 2019, 13, 34-38.	0.9	1
166	Highly Water-Repellent Nanostructure on Quartz Surface Based on Cassie-Baxter Model With Filling Factor. IEEE Open Journal of Nanotechnology, 2020, 1, 1-5.	0.9	1
167	High-Frequency Precise Characterization of Intrinsic FinFET Channel. IEICE Transactions on Electronics, 2012, E95.C, 752-760.	0.3	1
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